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AUTHOR CORRECTION

Correction to: Investigation on microstructure and improved supercapacitive performance of Mn doped CuO thin films prepared by reactive radio frequency magnetron sputtering

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The original version of the article unfortunately contained the following errors:

In Sect. 3, Results and Discussion – 3.1, X-ray diffraction analysis, the Miller indices (planes of CuO) should read as $(\bar{1}11)$, (111) and $(\bar{1}13)$ instead of (111), (111) and (113).

In Sect. 3.3, Microstructural analysis, Table 3 "Roughness parameter of CuO and Mn doped CuO films deposited on silicon substrate" the column head for 2nd and 3rd column should read as "Root mean square roughness (RMS) (nm)" and "Average roughness (Ra) (nm)". The correct table is given below.

Table 3 Roughness parameter of CuO and Mn doped CuO films deposited on silicon substrate

Sample	Root mean square roughness (RMS) (nm)	Average roughness (Ra) (nm)
CuO	8.63	6.32
Mn doped CuO	7.28	5.72

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